

Silicon NPN Power Transistors

2SC4057

DESCRIPTION

- With TO-247 package
- High voltage;high speed
- Switching power transistor

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

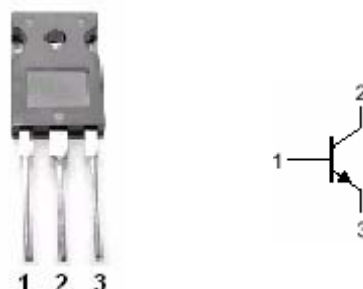


Fig.1 simplified outline (TO-247) and symbol

Absolute maximum ratings($T_c=25$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	600	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		8	A
I_{CM}	Collector current-Peak		16	A
I_B	Base current		4	A
I_{BM}	Base current-Peak		8	A
P_D	Total power dissipation	$T_c=25$	80	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal resistance junction to case	1.56	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A; I _B =0	450			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	At rated voltage			0.1	mA
I _{CEO}	Collector cut-off current					
I _{EBO}	Emitter cut-off current	At rated voltage			0.1	mA
h _{FE-1}	DC current gain	I _C =4A; V _{CE} =5V	10			
h _{FE-2}	DC current gain	I _C =1mA; V _{CE} =5V	5			
f _T	Transition frequency	I _C =0.8A; V _{CE} =10V		20		MHz

Switching times resistive load

t _{on}	Turn-on time	I _C =4A I _{B1} =0.8A; I _{B2} =1.6A V _{BB2} =4V, R _L =37.5			0.5	μs
t _s	Storage time				2.0	μs
t _f	Fall time				0.2	μs

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PACKAGE OUTLINE

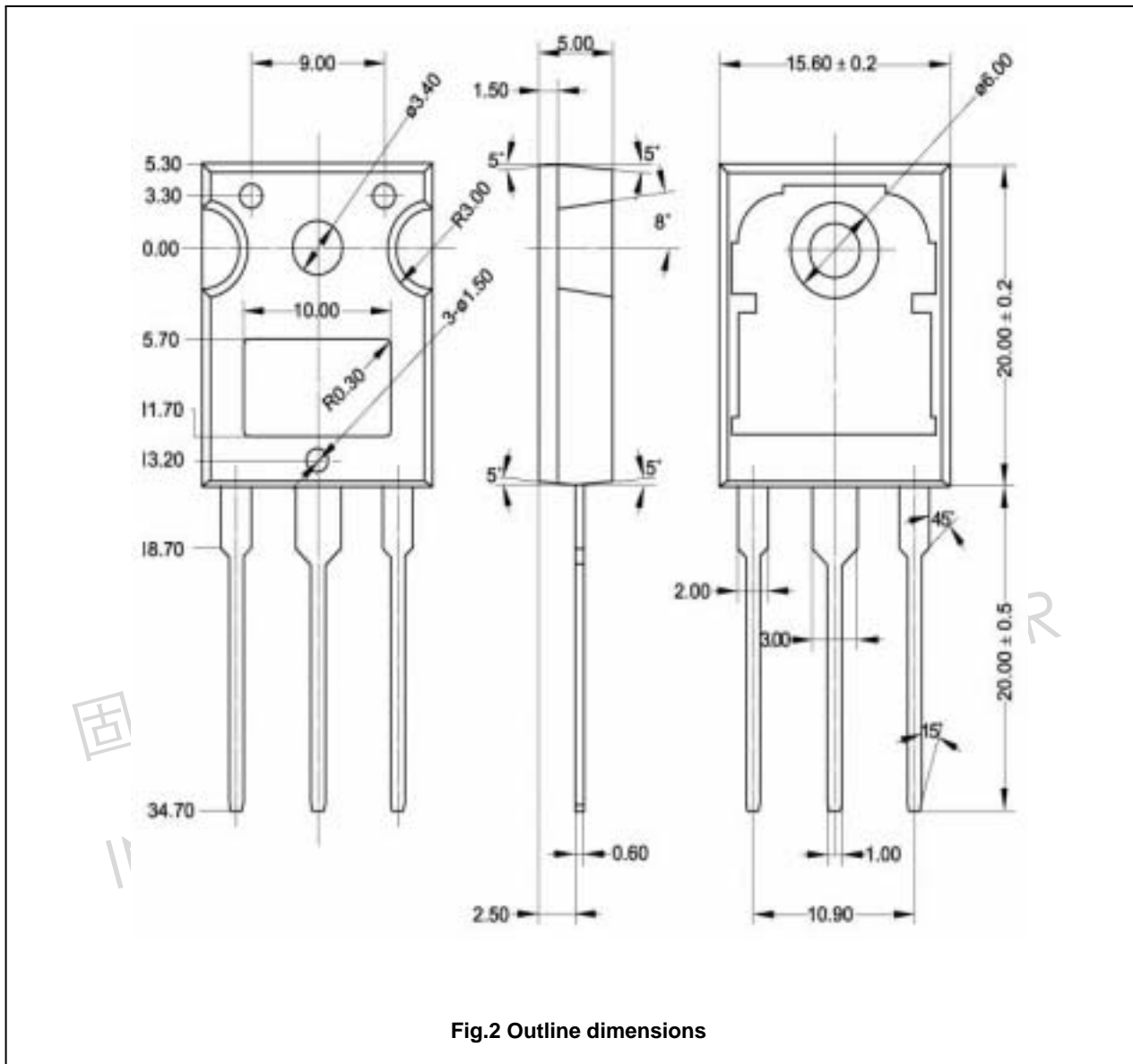


Fig.2 Outline dimensions